

LNC801PS

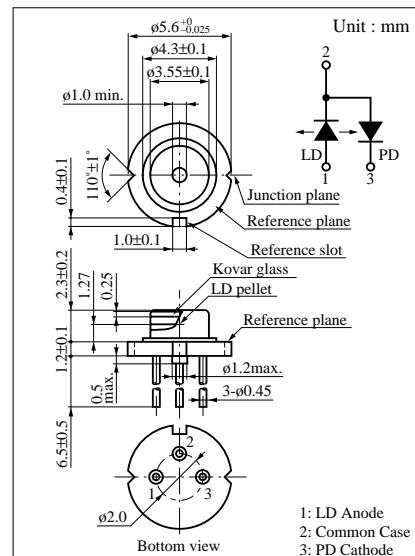
High Power Output Semiconductor Laser

■ Overview

The LNC801PS is a GaAlAs laser diode which provides stable, continuous, single mode oscillation of near infrared light at room temperature. This product can be used in a wide range of light source applications, including laser printers, facsimiles, optical disk memory, and optical information devices.

■ Features

- Low threshold oscillation
- Stable single horizontal mode oscillation
- Built-in PIN photodiode for light output monitors
- Light output is continuously variable as far as 60 mW
- Supports direct modulation
- Near infrared oscillating wavelength
- Long lifetime, high reliability



■ Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Ratings	Unit
Radiant power	P_O	60	mW
Reverse voltage	V_R	1.5	V
	V_R (PIN)	30	V
Power dissipation	P_d (PIN)	100	mW
Operating ambient temperature	T_{opr}	-10 to +60	°C
Storage temperature	T_{stg}	-40 to +80	°C

■ Electro-Optical Characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	min	typ	max	Unit
Threshold current	I_{th}	CW	10	30	50	mA
Operating current	I_{OP}	$P_O = 50\text{mW}$	50	70	120	mA
Operating voltage	V_{OP}	$P_O = 50\text{mW}$		2.0	3.0	V
Oscillation wavelength	λ_L	$P_O = 50\text{mW}$	815	830	845	nm
Radiation angle	Horizontal direction $\theta_{//}^*$	$P_O = 50\text{mW}$	7	10	13	deg.
	Vertical direction θ_{\perp}^*	$P_O = 50\text{mW}$	18	25	28	deg.
Differential efficiency	η	CW $P_O = 36\text{mW}/I(40\text{mW} - 4\text{mW})$	0.6	1.0	1.5	mW/mA
Reverse current (DC)	I_R	V_R (PIN) = 5V			0.1	μA
PIN photo current	I_P	$P_O = 50\text{mW}, V_R$ (PIN) = 5V				mA
Optical axis accuracy	X direction θ_X	$P_O = 50\text{mW}$	-2.0		+2.0	deg.
	Y direction θ_Y	$P_O = 50\text{mW}$	-3.0		+3.0	deg.
Oscillation mode		Single horizontal mode				

* $\theta_{//}$ and θ_{\perp} are the angles where the optical intensity is a half of its max. value.(half full angle)

